Emergence of dielectric anisotropy of crystalline Strontium Titanate due to temperature-dependent phase transitions

Zijun C. Zhao, Maxim Goryachev, Jerzy Krupka and Michael E. Tobar

aARC Centre of Excellence for Engineered Quantum Systems, School of Physics, University of Western Australia, 35 Stirling Highway, Crawley WA 6009, Australia; bInstytut Mikroelektroniki i Optoelektroniki PW, Koszykowa 75, 00-662 Warsaw, Poland

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ABSTRACT
We have undertaken precision measurements of permittivity of single crystal Strontium Titanate from 294.6 K to 5.6 K by measuring the frequency of multiple microwave transverse electric and magnetic resonant modes. Compared with conflicting results reported previously, we unequivocally show that the permittivity has an isotropic value of $316.3 \pm 2.2$ at room temperature, consistent with its well-known cubic structure. The onset of dielectric anisotropy at cryogenic temperatures was determined and shows that the crystal becomes uniaxial anisotropic below 105 K with a tetragonal structure, and biaxial anisotropic below 51K with an orthorhombic structure, when it undergoes several phase transitions.

KEYWORDS
dielectric properties; strontium titanate; anisotropic; phase transition; finite element simulation

1. Introduction

Strontium titanate (SrTiO$_3$) or STO has been a very popular material for study at low temperatures due to its unique properties. The crystal is a perovskite at room temperature and as it is cooled, undergoes a well-known cubic to tetragonal structural transition at 105 K. This antiferrodistortive (AFD) phase transition occurs due to the softening of a transverse optic phonon mode, which is very sensitive to axial stress [1,2]. Below this temperature the properties can depend on how the sample is cooled, for example if it is stressed or has a voltage applied the properties can be significantly affected [3-11]. The crystal approaches a ferroelectric phase at 51 K, however quantum fluctuations of the low frequency phonon modes prevent it from completely undergoing the corresponding phase transition, becoming a quantum paraelectric at 5K [1], unless an external stress or voltage is applied [2,12]. Since the discovery, there has been a number of attempts to study this phenomena at low temperatures both theoretically [9,12] and experimentally [15,16,13,20].

Importantly, the high permittivity and large dependence of permittivity on electric field is an important characteristic for STO, which allows device miniaturisation and small mode volume devices. Examples includes room temperature masers [21] and...
the voltage control of superconducting electronic devices \cite{22}. Further utilisation of STO in various fields of low temperature physics has lead to extensive studies of its electromagnetic properties. It was recently determined that anisotropy below the AFD phase transition occurs due to a trilinear coupling between the polarisation, AFD lattice tilts and an antiferroelectric (AFE) mode \cite{23}. In this work, we characterise the microwave permittivity of a cylindrical crystalline STO sample, grown along its cylindrical axis, and show that the permittivity is isotropic at room temperature by measuring multiple modes of different electric field polarisations. As the crystal is cooled we unequivocally show the material first becomes uniaxially anisotropic at 105 K and then biaxially anisotropic at 51 K. These results give important information for designing devices over this temperature range, which utilise the unique properties of STO.

Dielectric characterisation of materials using multiple modes in a single resonant structure has become a successful technique for uniaxial \cite{24,25} and biaxial permittivity determination \cite{27,28}. These techniques use a combination of low order Transverse Electric (TE) and Transverse Magnetic (TM) modes, as well as higher order modes such as Whispering Gallery Modes (WGM) to successfully characterise the anisotropy. The main advantages of this technique is due to the use of a large number of modes in the centimetre and millimetre wave frequency ranges with varying mode polarisation and high magnetic and electrical filling factors within the sample. Due to these properties WGM devices have also been implemented to characterise material electromagnetic loss and allow the comprehensive Electron Spin Resonance (ESR) spectroscopy of various ions within different crystals using the multiple modes \cite{29,35}. Recently this technique was applied to an STO crystal, which measured extra dielectric losses at microwave frequencies at temperatures below the the ferroelectric phase transition temperature at 51 K \cite{36}, consistent with previous measurements \cite{14,16}.

2. Materials and methods

2.1. Microwave cavity for STO

In order to probe the dielectric properties of STO, a cylindrical crystal specimen of diameter 3.27 mm and height 3.66 mm was utilised. The crystal was put in a cylindrically symmetric oxygen free copper cavity with diameter of 8 mm and height of 4.7 mm. The crystal was placed on top of a sapphire disk substrate and kept in place by a teflon piece on top, as demonstrated in Fig. 1 inset. The sapphire substrate and the teflon piece were utilised in order to uncouple the crystal modes from the cavity walls and, thus, to increase the quality factor of the modes. Sapphire was chosen on the bottom of the cavity due to its low dielectric loss and good thermal conductivity at low temperatures. On the other hand, these materials do not introduce any significant error to the measurement results due to orders of magnitude difference in permittivity with the STO crystal. Microwave radiation in the cavity was excited via both straight electrode antenna and loop probes separately in order to resolve modes of TE and TM polarisations.

2.2. Finite element simulation

To calculate resonant mode frequencies for comparison with experimental measurements, finite element simulation by COMSOL Multiphysics was implemented to study
the resonator in Fig. 1 inset. This model utilised known parameters of all materials except for the STO crystal. To calculate material properties of STO at room temperature and cryogenic temperatures, the permittivity was iterated in the model to minimise the error between the calculated and measured frequencies for the selected modes.

2.3. Frequency measurements at room temperature and cryogenic temperatures

The system was characterised in transmission ($S_{21}$) with a vector network analyser (VNA). At room temperature, resonance mode frequencies were found by searching manually in the range of 4 to 20 GHz and identified by comparison with the simulation, with comparisons shown in Fig. 1. For the considered structure, only modes with $m = 0$ can be pure TM or TE polarisation, for $m > 1$ the modes are quasi TE and TM and become WGM as $m$ increases. The lowest four modes in frequency of the fundamental quasi TE and TM mode families were measured with azimuthal mode numbers of up to $m = 4$.

For cryogenic measurements, the copper cavity was attached to the 4K plate of a cryogen free pulsed tube system and measured in $S_{21}$ with VNA. In order to measure the temperature dependence, a Cernox calibrated thermometer was attached to the copper cavity and continuously measured throughout the experiment. Measurements were implemented by warming up and cooling down very slowly in thermal equilibrium, with temperature lag between the thermometer and crystal kept to a minimum. The first TE and TM modes were identified from the temperature measurements and used for the permittivity calculations.

Figure 1. Comparison between measured and calculated frequencies of the fundamental quasi-TE and TM mode families with the a STO permittivity of 316.3. Inset: Side view or $(r, z)$ plane of the STO cylindrical cavity. The cylindrical crystal is mounted on a sapphire disc substrate and held in place by a teflon piece.
3. Results and discussion

3.1. Characterisation at Room Temperature

At room temperature, it is well known that STO exhibits a cubic structure and therefore is most likely isotropic. Despite this, early work that implemented a capacitive technique using single crystal wafers between 0.125 and 1mm thickness in various crystal orientations, reported anisotropy at room temperature [5]. Gold electrodes were deposited on the samples and the permittivity was inferred from 4.2 K to 300 K and between 1 kHz to 50 MHz. Their permittivity measurements yield 330 in the [001] direction, 458 in the [011] direction and 448 in the [111] direction at room temperature. This type of scatter in measurements with only a ± 2% error and is not consistent with our isotropic value. In the next section we compare our results across the whole temperature range and discuss the most likely discrepancies between our measurements and the ones presented in [5].

Fig. 1 shows clearly good agreement for the fundamental TM and TE mode families, with the value 316.3 as isotropic permittivity minimising the aggregate error between simulation and experiment. The cylindrically symmetric permittivity gives the average error of the four TE modes to be 0.18% while the average of the four TM modes to be 0.52%. Also, dimensions were measured to the nearest hundreth of a mm using laser technique giving approximately 0.3% error in height and radius. Adding all errors in quadrature gives a value of permittivity of 316.3 ± 2.2, consistent with more recent measurements of permittivity, which have only implemented TE modes [16,21]. The mode free-spectral range is nearly constant and close to 2 GHz and the permittivity was demonstrated to be effectively constant and shows no frequency dependence from 4 to 11 GHz. This result is consistent with the soft mode phonon theory, which dominates the value of permittivity in this frequency range [5]. Prior work predicts the permittivity to be constant beyond a THz at room temperature and beyond 100 GHz at 4.2 K [5].

3.2. Revealing Crystal Anisotropy at Cryogenic Temperatures

The frequency versus temperature measurements are shown in Fig. 2. The lowest frequency modes are measured and identified as TE_{0,1,1} mode and the quasi TM_{1,1,1} / TM^*_{1,1,1} modes. As the temperature goes down, TM and TE modes diverge in frequency below 110K and the TM_{1,1,1} doublet degeneracy is lifted below 51K. Due to the non-zero value of m for the TM_{1,1,1} mode, the resonance is in principle degenerate. The doublet degeneracy will be lifted if the permittivity is biaxial, and this effect has recently been used to characterise biaxial material [27]. It is clear from the temperature dependence observed of the mode frequencies as shown in Fig. 2 that the material exhibits uniaxial anisotropy at 105 K, and then biaxial anisotropy in permittivity at 51 K.

Due to the high dielectric constant of the STO, the electrical energy is mostly confined within the crystal and filling factors are approximately constant across a wide temperature range. Filling factors were calculated from the COMSOL simulation for each mode. At room temperature, for the TM_{1,1,1} mode the electrical energy filling factor parallel to the c-axis is $P_{c||} ≈ 63\%$ and perpendicular is $P_{c⊥} ≈ 37\%$, while for the TE_{0,1,1} mode it is $P_{c||} = 0\%$ and $P_{c⊥} ≈ 100\%$. Thus, previous measurements that utilised TE modes of $m = 0$ only determine the perpendicular component of permittivity [14,16]. In this paper, this is overcome by simultaneously measuring the
Figure 2. Left: Color density plot of experimental measurements of $S_{21}$ versus temperature below 30 K. TE$_{0,1,1}$ mode and the quasi TM$_{1,1,1}$ / TM$_{1,1,1}$ modes are identified. The discontinuity of TE$_{0,1,1}$ around 12 K is due to the mode crossing caused by anisotropy at low temperatures of STO, which leads to different temperature coefficients of TM and TE modes. Right: Frequency versus temperature for the TE$_{0,1,1}$ mode and the quasi TM$_{1,1,1}$ / TM$_{1,1,1}$ modes. The solid dots represents experimental measurements of frequency, while the line represents polynomial fits. The hollow circles represent results from the finite element simulation. Due to the high permittivity of the STO, electrical energy is mostly confined within the crystal with filling factors of each mode summing up close to unity (or 100%) across the whole temperature range.

TE$_{0,1,1}$ and TM$_{1,1,1}$ modes, the latter of which couples to both anisotropy directions, but more strongly to the parallel component. Thus, through numerical iteration both components of permittivity can be found here. With the additional data of TM$_{1,1,1}$ mode, the anisotropy in perpendicular component of the permittivity is also revealed.

Figure 3. Left: Derived permittivities $\varepsilon_x$, $\varepsilon_y$ and $\varepsilon_z$ from the frequency measurement in Fig. 2 and the finite element simulation, with comparison to measurements from Ref[5] along different crystallographic directions. Right: Normalized permittivities $\varepsilon_x$, $\varepsilon_y$ and $\varepsilon_z$ versus temperature. Each permittivity is normalized by dividing a value of $\sqrt{\varepsilon_x^2 + \varepsilon_y^2 + \varepsilon_z^2}$.

The values of permittivity derived from the curve fits in Fig. 2 and the finite element modelling are shown in Fig. 3 are compared with data from literature [5]. Our results show a significant change in anisotropy, which can be explained by crystal structure phase transitions. Plots in Fig. 3 are subdivided into sections A-D in accordance with corresponding phases. From room temperature down to 110K, STO exhibits highly symmetric cubic perovskite structure (space group Pm3m) as demonstrated by section
A. For lower temperatures, the crystal structure is deformed from cubic by a number of effects. STO demonstrates tetragonal (space group I4/mcm) structure in the range 110 – 51K (section B) shifting to orthorhombic in the range 51 – 35K (section C). Also, it has been demonstrated that at 10K, STO forms a single low-symmetry phase (section D), which is possibly a rhombohedral structure\cite{2,17}. It is evident from Fig. 3 that the main transition to biaxial anisotropy occurs when the crystal structure shifts to the orthorhombic phase.

The results in \cite{5} do not show any clear anisotropy as originally claimed, and the varying results are most likely due to systematic scatter of data due to dimensional and other errors. Also, below 50 K the results of\cite{5} are not clearly anisotropic either, and in general give a lower value of permittivity below 15 K than those measured in this work. It has been shown that the application of stress to the crystal lowers the permittivity of the crystal \cite{1}, and that the permittivity of STO is highly stress dependent. We postulate that the results of \cite{5} had excess stress created in the crystal due to the differential contraction of the gold electrodes deposited on the crystal. Our technique is stress free as the crystal sits on a sapphire substrate, with an indentation slightly bigger than the crystal radius to keep the crystal in place, along with a loosely fitting teflon cap held from the top of the cavity.

4. Conclusions

In summary, precision measurement of the permittivity is undertaken by continuously measuring multiple TE and TM resonant modes within a single crystal dielectrically loaded microwave cavity resonator in thermal equilibrium from 5.6 K to room temperature. It is shown that the permittivity is isotropic at room temperature with a value of 316.3 ± 2.2 by measuring multiple modes of different electric field polarisations. The SrTiO$_3$ crystal underwent two displacive phase transitions around 105 K and 51 K. The temperature dependent permittivity obtained for the SrTiO$_3$ crystal is consistent with the known transformations of the crystal structure during these transitions. The crystal becomes uniaxially anisotropic below the antiferrodistortive phase transition at 105 K, when the lattice transforms from cubic to tetragonal, and then biaxially anisotropic below the ferroelectric phase transition at 51 K, when the lattice transforms from tetragonal to orthorhombic. We also show that precision measurements of the frequency of multiple modes is a practical technique to study phase transitions in high permittivity ferroelectric crystals.

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References


